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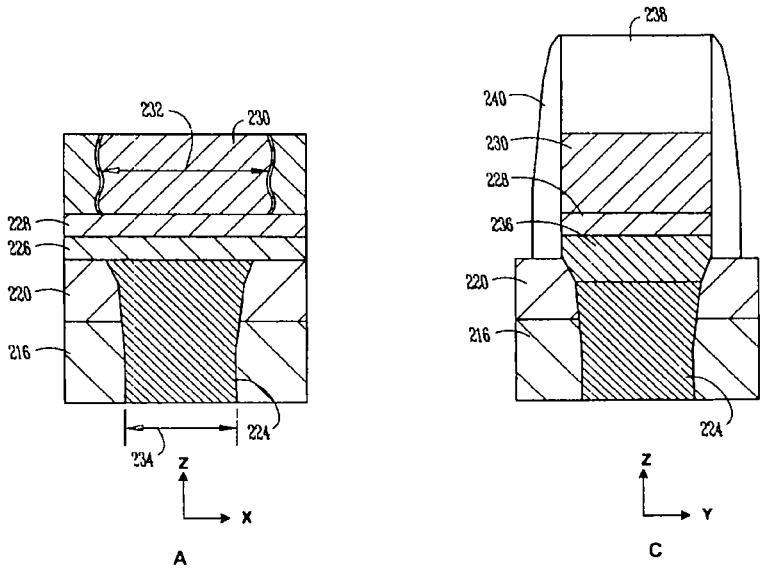
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(54) Title: BURIED DIGIT LINE STACK AND PROCESS FOR MAKING SAME



(57) Abstract: A process of making a buried digit line stack is disclosed. The process includes forming a silicon-lean metal silicide first film (226) over a polysilicon plug (224), followed by a silicide compound barrier second film (228). The silicide compound barrier second film is covered with a refractory metal third film (232). A salicidation process causes the first film to salicide (236) with the polysilicon plug. In one embodiment, all the aforementioned deposition processes are carried out by physical vapor deposition ("PVD").

WO 03/103046 A1

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